

**SEMICONDUCTOR DEVICE AND ITS DRIVING METHOD**

**Publication number:** JP2001308306 (A)

**Publication date:** 2001-11-02

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**Classification:**

- **international:** G01J1/02; H01L27/14; H01L27/146; H01L29/786; H01L31/10; H04N5/335; H01L31/10; G01J1/02; H01L27/14; H01L27/146; H01L29/66; H01L31/10; H04N5/335; H01L31/10; (IPC1-7): H01L27/146; G01J1/02; H01L27/14; H01L29/786; H01L31/10; H04N5/335

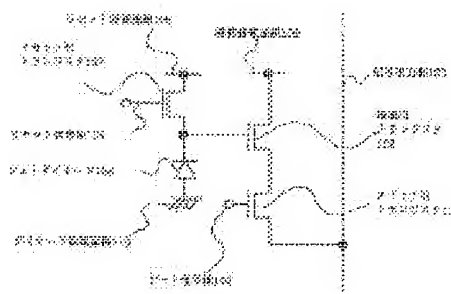
- **European:**

**Application number:** JP20000120920 20000421

**Priority number(s):** JP20000120920 20000421

**Abstract of JP 2001308306 (A)**

**PROBLEM TO BE SOLVED:** To provide a semiconductor device that can reduce the influence of current leaking from a transistor for resetting to a photoelectric conversion element, and the driving method of the semiconductor device. **SOLUTION:** In this semiconductor device and its driving method, the semiconductor device has the transistor for resetting, the photoelectric conversion element, and reset- and diode-side power lines, and the potential of the reset-side power line is brought closer to that of the diode-side power line when the transistor for resetting does not conduct electricity.



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